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Current-temperature Characteristics of Low-temperature-sputtered (Ba, Sr)TiO$_3$ Films Post Treated by Rapid Thermal Annealing

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ABSTRACT

This work reports the current-temperature characteristics of the low-temperature-sputtered (Ba$_{0.8}$Sr$_{0.2}$)TiO$_3$ (BST) film post treated by rapid thermal annealing (RTA) in O$_2$ ambient. The top electrode was biased under negative/positive voltage to investigate the interface properties of the Pt/BST/Pt multilayer. As the results, the current density of the RTA-treated BST film was greatly reduced owing to compensation of oxygen vacancies. The RTA-treated BST thin film biased at negative voltage exhibits a negative temperature-coefficient-resistivity (NTCR) behavior, but, intriguingly, that biased at positive voltage reveals a positive temperature-coefficient-resistivity (PTCR) behavior. According to the leakage current analysis, the Schottky emission dominates the negative biased current at upper interface, but the Heywang barrier scattering confines the positive biased current.

Keywords: (Ba$_{0.8}$Sr$_{0.2}$)TiO$_3$, rapid thermal annealing (RTA), NTCR, PTCR, Schottky emission, Heywang barrier
INTRODUCTION

Recently, the high temperature-coefficient-resistivity (TCR) thermistors are widely applied as thermal detectors owing to their low cost and excellent responsivity [1]. In general, the thermistor using positive TCR (PTCR) material can prevent the effect of thermal-run-away, so the complementary circuits can be simplified [2]. Since the abnormally high PTCR of BaTiO$_3$ (BTO) ferroelectric materials was observed at Curie temperature (Tc) in 1955 [3], the conduction mechanisms and applications of these perovskite films have attracted great attention in the past decades. The substitution of Sr for Ba in BTO solid solution, forming the (Ba,Sr)TiO$_3$ (BST), can effectively adjust the Currie temperature to obtain a proper operation condition for a device.

The high TCR thin film is employed on microthermistor array using the fabrication technique of microelectromechanical-system (MEMs) as an infra-red (IR) image sensor. Low temperature process is indeed necessary for the integration of the high TCR film into the MEM system, because a high temperature process will damage the under-layer structures of MEMs and junction profile of ICs. In this study, the low-temperature-prepared BST films were post treated by rapid thermal annealing (RTA) to achieve excellent electric properties. However, the TCR phenomenon of the bulk BST is discussed in many works, but very few works have reported the TCR effect of the thin BST film [4]. The conduction current of BST was measured in the temperature ranging from room temperature to 410°K, and the conduction mechanisms were systematically investigated.

EXPERIMENTAL

A testing structure of Pt/BST/Pt/TiN/Ti multifilm resistor with intercrossing top/bottom electrodes was employed for TCR measurement, as shown in Figure 1. In general, an extra thermal expansion stress is caused by directly probing on the heated-BST film, so the intercrossing electrodes prevents the unwanted disturbance from TCR measurement. The testing area (20×20μm$^2$) of this thin multifilm is defined by the overlap between the top and bottom
Figure 1. The testing structure of Pt/BST/Pt/TiN/Ti multilayer with intercrossing top/bottom electrodes.

electrodes, and both of top and bottom electrodes are patterned by using the liftoff technique.

The Pt/TiN/Ti multilayer with 100nm/50nm/10nm, serving as the metal/barrier/adhesion layer, was sputtered onto the SiO₂/Si substrate at room temperature. Ba₀.₆Sr₀.₄TiO₃ film (300nm) was then deposited using a RF magnetron co-sputtering system at a substrate temperature of 300°C. The BST films were subsequently post treated by RTA 400°C (5 minutes) and 500°C (1 minute).

The current-temperature characteristic was studied by using the Pt/BST/Pt

Figure 2. The conduction current of Pt/BST/Pt with various RTA temperatures measured at 320°C.
(metal-insulator-metal, MIM) structure. An automatic measurement system that combines HP 4156A and a probe station was conducted to obtain the current-voltage (I-V) characteristics of BST resistors. The current-temperature testing was carried out using a hot plate.

RESULTS AND DISCUSSION

Figure 2 presents the leakage current of BST films post treated at various RTA temperatures. In general, the conduction current of BST film is induced by oxygen vacancies according to $O_0 \leftrightarrow V_0^{\text{++}} + 2e^- + 1/2O_2$, where $O_0$, $V_0^{\text{++}}$ and $e^-$ denote the oxygen ion at its normal site, oxygen vacancy and electron, respectively. However, a higher concentration of oxygen vacancies leads to n-type conductivity of the BST materials due to the generated electrons, causing larger conduction currents [5]. The conduction current of BST film with post RTA treatment in oxygen ambient is suppressed due to oxygen vacancies compensated by $O_2$ ambient gas.

![Figure 3. TCR of BST films (a) without post treatment and (b) with post RTA treatments at 500°C under -3 volts.](image-url)
Figure 4. The log ($J/T^2$) versus $E^{1/2}$ plot showing Schottky emission fitting for the BST films under negative bias.

Figure 5. The log ($J/T^2$) versus $1/T$ plot showing Schottky emission fitting for the BST films treated (a) without RTA and (b) with RTA at 500°C under negative bias.

The temperature-coefficient-resistivity (TCR) is defined as $TCR = \left. \frac{1}{R_s} \frac{dR_s}{dT} \right|_T$, where $T$ and $R_s$ represent the temperature and the resistance. Figure 3 indicates the TCR of BST films (a) without post treatment and (b) with post RTA treatments at 500°C. Both the films behave NTCR at a bias of -3 volts.

The conduction mechanisms of metal/BST/metal capacitors are usually interpreted as interface-limited and bulk-limited conduction [6]. In general, the Schottky emission (SE) governs the interface-limited current for the Pt/BST
films. The leakage current governed by SE behavior is expressed as [7],

$$\log \left( \frac{J_{SE}}{T^2} \right) = -q \phi_B - \frac{qE}{4\pi \epsilon_d} \sqrt{\epsilon_c} \left[ \sqrt{\frac{kT}{\epsilon_d}} \ln 10 \right] + \log(A^*) \tag{1}$$

where, $A^*$ is the effective Richardson's constant; $\phi_B$ is the potential barrier height at the surface; $\epsilon_d$ is the dynamic dielectric constant of the ferroelectric material in the infrared region; $q$ is the unit charge; $k$ is Boltzmann's constant; $T$ is temperature, and $E$ is the external electric field. Figure 4 shows that both the plots of $\log(J/T^2)$ against $E^{1/2}$ exhibit linear relations under negative bias. In addition, the plots of $\log(J/T^2)$ against $1/T$ exhibit linear relations, too, as shown in Fig. 5. Consequently, both the samples biased at negative voltage show the Schottky emission behavior.

The BST film without RTA treatment exhibits NTCR under positive bias, as shown in Fig. 6 (a), but the films treated with RTA at 500°C reveals PTCR in the range of current-measurement-temperature from room temperature to 330°K, as shown in Fig. 6 (b). The BST film treated without RTA exhibits SE behaviors.

![Figure 6](image_url)

**Figure 6.** TCR of BST films (a) with RTA treatment and (b) with RTA treatment at 500°C under +3 Volts.
Figure 7. The log \((J/T^2)\) versus \(1/T\) plot showing Schottky emission fitting for the BST films treated (a) without RTA and (b) with RTA at 500°C under positive bias.

but the film treated with RTA at 500°C doesn't exhibit SE behavior at all, as shown in Fig. 7.

As mentioned above, the upper surface of BST film post treated by RTA in oxygen ambient is dominated by SE behavior under a negative bias. Hence, the negative-biased conduction current exhibits NTCR phenomenon according to the current-temperature relation of Eq. (1). On the other hand, the 500°C RTA treatment applied on BST/Pt films will behave a large thermal stress due to the temperature abruptly decreasing, and thus many interface states are induced at the interface of BST/Pt-bottom-electrode. The injected electron current, governed by the bulk-limited mechanism, is formed by the thermal-stress-induced interface states, and this bulk-limited conduction current film is confined by the Heywang barrier scattering [8]. The resistivity for the Heywang model are represented as \(R_s \propto \exp(-q\phi/kT)\) and \(\phi = \frac{e^2 N_d d^2}{2\varepsilon \varepsilon_0}\), where \(\phi\) and \(d\) are the potential height and depletion width at grain boundary, so the resistivity increases as temperature rises. Thus, the RTA-treated BST film reveals PTCR phenomenon under positive bias.
CONCLUSIONS

The post RTA treatment in oxygen ambient can greatly suppress the conduction current for the Pt/BST/Pt films owing to the compensation of the oxygen vacancies. In this work, both of the Pt/BST/Pt multilfilms reveal NTCR behavior under negative bias, but the sample treated by RTA exhibits PTCR behavior under positive bias. The results of the SE fitting indicate the Schottky barrier formed at upper interface, which results in the NTCR phenomenon for the sample biased at negative voltage. On the other hand, the thermal-stress-induced interface states cause the injected electron current, which is confined by Heywang barrier scattering. Hence, the positive biased BST film with RTA treatment reveals the PTCR phenomenon.

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REFERENCES
